

PMV33UPE

20 V, single P-channel Trench MOSFET Rev. 1 — 12 June 2012

Product data sheet

Product profile 1.

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching

- Trench MOSFET technology
- 2 kV ESD protected

1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25$ °C		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-	-5.3	Α
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -3 \text{ A}; T_j = 25 \text{ °C}$		-	30	36	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



2. Pinning information

Table 2. Pinning information

Pin	Cymbol		Simplified outline	Graphic symbol
Pilli	Symbol	Description	Simplified outline	Graphic Symbol
1	G	gate		D
2	S	source	3	
3	D	drain	1	G S 017aaa259

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PMV33UPE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23	

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMV33UPE	EJ%

[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-5.3	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	<u>[1]</u>	-	-4.4	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	<u>[1]</u>	-	-2.8	Α
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \text{ µs}$		-	-17.6	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	490	mW
			<u>[1]</u>	-	980	mW
		T _{sp} = 25 °C		-	4150	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-1.2	Α
ESD maxim	um rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

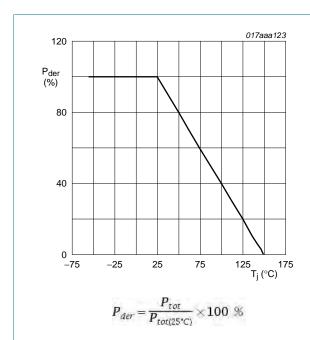


Fig 1. Normalized total power dissipation as a function of junction temperature

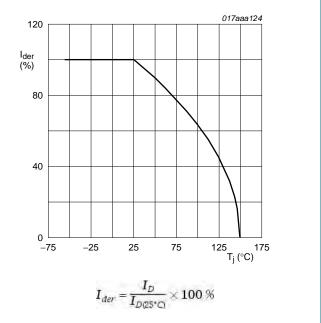


Fig 2. Normalized continuous drain current as a function of junction temperature

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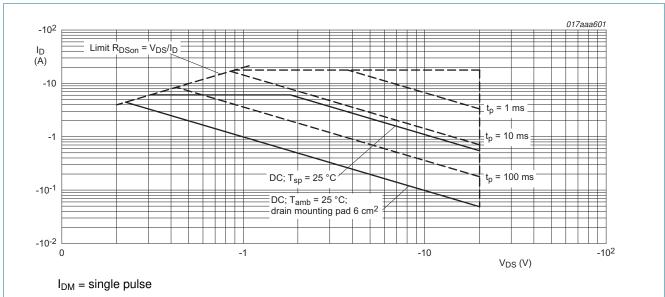


Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance		<u>[1]</u>	-	222	255	K/W
	from junction to ambient		[2]	-	111	128	K/W
	ambient		[3]	-	74	85	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	25	30	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², t ≤ 5 s.

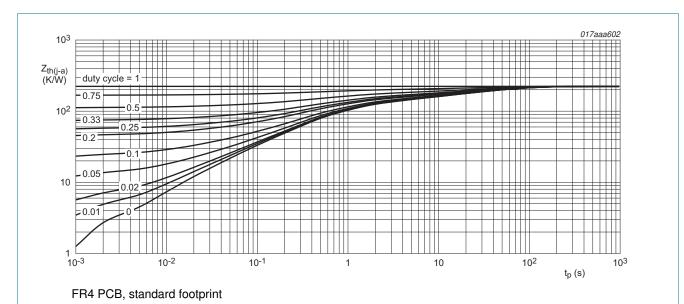


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

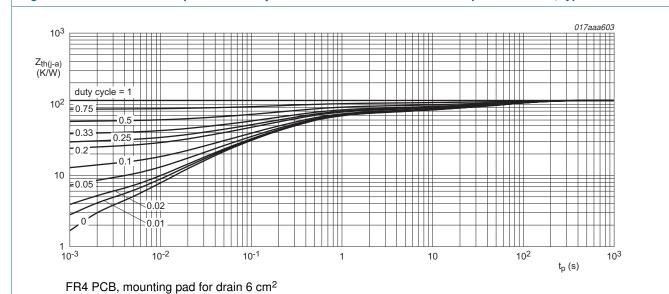


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-15	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
		$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-10	μΑ
R _{DSon}	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -3 \text{ A}; T_j = 25 \text{ °C}$	-	30	36	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -3 \text{ A}; T_j = 150 \text{ °C}$	-	43	51	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -3 \text{ A}; T_j = 25 \text{ °C}$	-	38	47	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -3 \text{ A}; T_j = 25 \text{ °C}$	-	51	65	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -4.4 \text{ A}; T_j = 25 \text{ °C}$	-	16	-	S
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -4.4 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	14.7	22.1	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	2.6	-	nC
Q_{GD}	gate-drain charge		-	2.5	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V;}$	-	1820	-	pF
C _{oss}	output capacitance	$T_j = 25 ^{\circ}C$	-	208	-	pF
C_{rss}	reverse transfer capacitance		-	146	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -10 \text{ V}; I_D = -4.4 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	11	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	30	-	ns
t _{d(off)}	turn-off delay time		-	83	-	ns
t _f	fall time		-	39	-	ns
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = -1.2 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_i = 25 \text{ °C}$	-	-0.7	-1.2	V

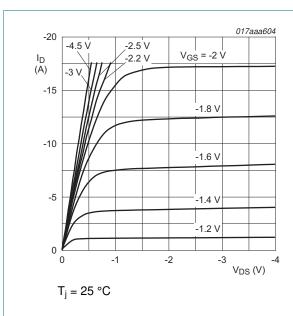


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

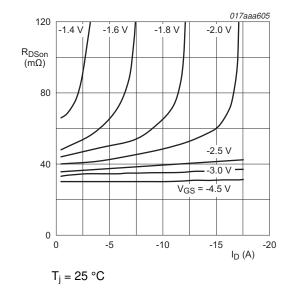
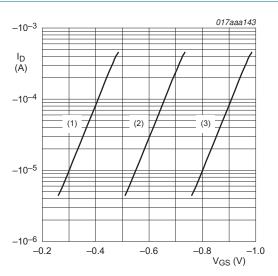


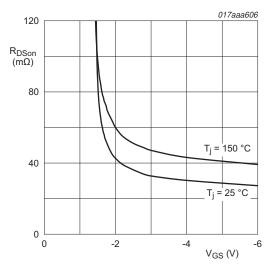
Fig 8. Drain-source on-state resistance as a function of drain current; typical values



$$T_i = 25 \, ^{\circ}C; \, V_{DS} = -3 \, V$$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = -4.4 A$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

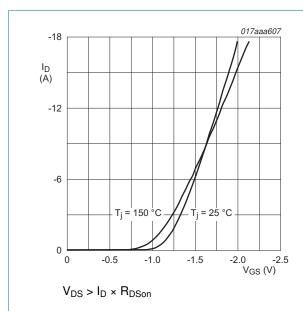


Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

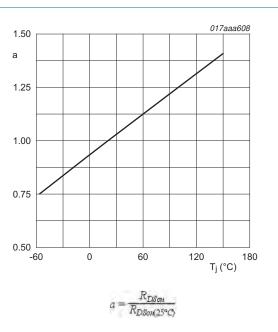
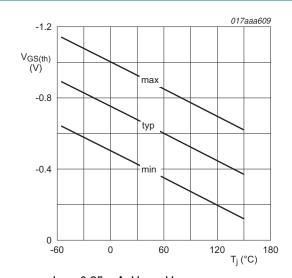
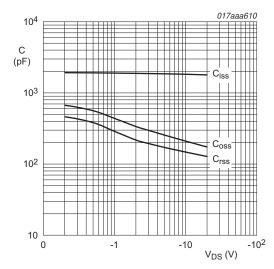


Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



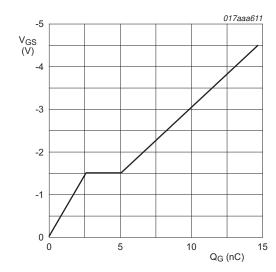
 I_D = -0.25 mA; V_{DS} = V_{GS}

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $I_D = -4.4 \text{ A}; V_{DS} = -10 \text{ V}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 14. Gate-source voltage as a function of gate charge; typical values

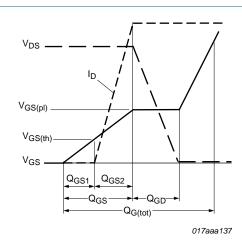
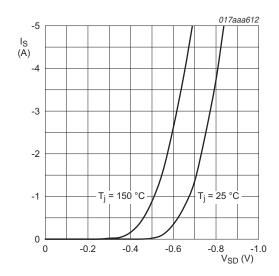


Fig 15. Gate charge waveform definitions

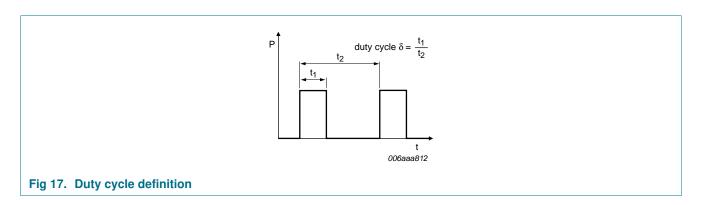


 $V_{GS} = 0 V$

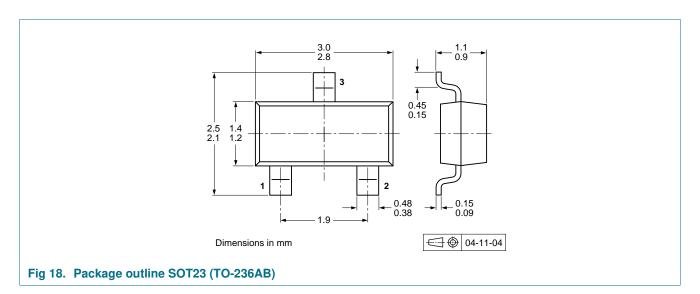
Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information

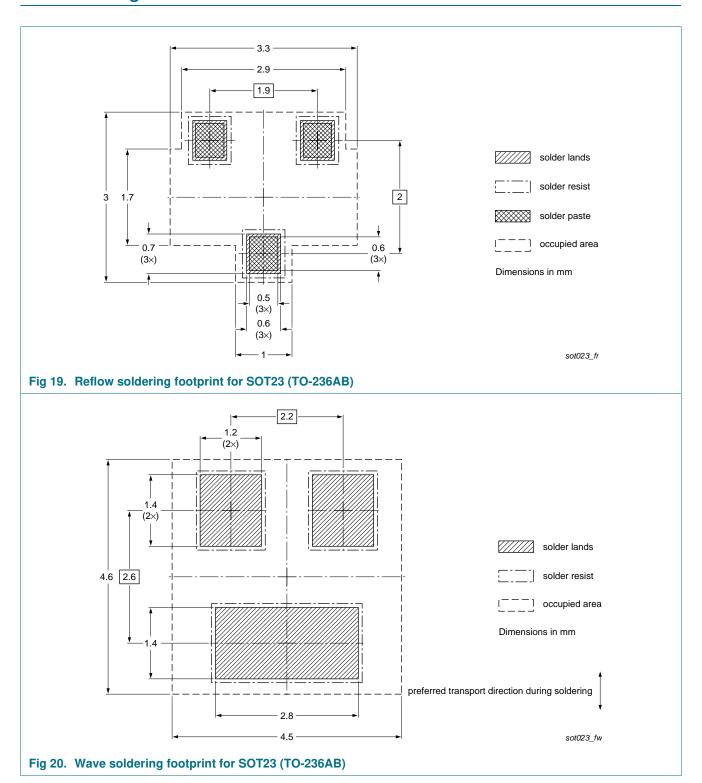


9. Package outline



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10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMV33UPE v.1	20120612	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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